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This listing presents the papers in alphabetical order of the first author, subdivided according to the groupings "Solids and Materials" and "Surfaces, Interfaces, and Layer Structures". The author index that follows covers APPLIED PHYSICS A and B, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second column the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The fourth column states the major PACS number so that the topic of the paper can be inferred by consulting the PACS listing on the left page.

SOLIDS and MATERIALS

- Ahmad M., Zihlif A.:
Effect of mechanical tension on electrical transport properties of amorphous Fe₉₂Zr₈ alloy.
Appl. Phys. A 45/3, 203-205 (1988) PACS: 72.15
- Barringer E.A., Bowen H.K.:
Effects of particle packing on the sintered microstructure.
Appl. Phys. A 45/4, 271-275 (1988) PACS: 81.20E 81.20
- Böhm M., Salamon S., Kiss Z.:
Amorphous silicon logic integrated circuits.
Appl. Phys. A 45/1, 53-61 (1988) PACS: 61.40 85.30 85.60
- Cantarero A., Martinez-Pastor J., Segura A., Chevy A.:
Excitonic absorption and Urbach's tail in bismuth sulfide single crystals.
Appl. Phys. A 45/2, 125-132 (1988) PACS: 78.20D 71.35
- Feila R., Rodek E.:
Phase transformation in a glass-ceramic observed by laser spectroscopy.
Appl. Phys. A 45/3, 185-187 (1988) PACS: 61.40 66.30 78.00
- Grader G.S., Gallagher P.K., Thomson J., Gurvitch M.:
Rates of change in high temperature electrical resistivity and oxygen diffusion coefficient in Ba₂YCu₃O_x.
Appl. Phys. A 45/3, 179-183 (1988) PACS: 74.00 66.30 82.20
- Ito Y., Takano T., Hasegawa M.:
Positron annihilation in synthetic zeolites. Comparison between lifetime and angular correlation data.
Appl. Phys. A 45/3, 193-201 (1988) PACS: 78.70D 81.90
- Jones K.S., Prussin S., Weber E.R.:
A systematic analysis of defects in ion-implanted silicon.
Appl. Phys. A 45/1, 1-34 (1988) PACS: 61.80 81.40
- Leo K., Rühle W.W., Queisser H.J., Ploog K.:
Hot carrier cooling in GaAs quantum wells.
Appl. Phys. A 45/1, 35-39 (1988) PACS: 72.10D 78.55
- Mazzone A.M.:
Dose effects in ion implanted compound semiconductors.
Appl. Phys. A 45/2, 113-118 (1988) PACS: 61.80 61.70
- McElfresh M.W., Maple M.B., Yank K.N., Fisk Z.:
Onset of superconductivity at 107 K in YBa₂Cu₃O_{7-δ} at high pressure.
Appl. Phys. A 45/4, 365-368 (1988) PACS: 74.70V
- Müller G.:
On the generation and annealing of dangling bond defects in hydrogenated amorphous silicon.
Appl. Phys. A 45/1, 41-51 (1988) PACS: 66.30L 68.60 72.80
- Müller G.:
Equilibrium dangling bond densities in a-Si:H and its related thin film alloys.
Appl. Phys. A 45/2, 103-107 (1988) PACS: 71.55 72.80
- Paprocki K., Bryłowska I., Syszko W.:
Depth distributions of Au recoil atoms in silicon.
Appl. Phys. A 45/2, 109-112 (1988) PACS: 61.10T 79.20
- Politis C.:
High-Tc superconductivity in the multi phases Sr-Bi-Ca-Cu-O.
Appl. Phys. A 45/3, 261-263 (1988) PACS: 74.40V
- Sharma S.K., Banerjee S., Kuldeep, Jain A.K.:
Diffusion of Au and Cu in amorphous Fe₈₀B₂₀ and Fe₈₂B₁₈ alloys.
Appl. Phys. A 45/3, 217-220 (1988) PACS: 66.30 61.40
- So F.C.T., Kolawa E., Nieh S.C.W., Zhao X.-A., Nicolet M.-A.:
Properties of reactively sputtered Mo(1-x)O_x films.
Appl. Phys. A 45/4, 265-270 (1988) PACS: 81.15 81.60

Stafast H.:

- Initial steps in the photochemical vapour deposition of amorphous silicon.
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- Sugioka K., Toyoda K.:
Influence of laser fluence and the dopant gas pressure on the properties of photochemical doping of Si into GaAs using XeCl excimer laser.
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- Tabib-Azar M., Das P.:
Acoustoelectric measurements of minority and majority carrier mobilities in semiconductors including Hg(1-x)Cd_xTe.
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Damage distribution in Si⁺-implanted gallium arsenide-lattice imaging.
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- Waldeer K.T., Urbassek H.M.:
Collision cascade evolution in media with energy independent scattering: Spatial energy and angular distribution.
Appl. Phys. A 45/3, 207-215 (1988) PACS: 79.20N 05.60

SURFACES, INTERFACES, and LAYER STRUCTURES

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Phase shift analysis of modulated photocurrent: Determination of the energy scale.
Appl. Phys. A 45/3, 221-224 (1988) PACS: 72.40
- Bentini G.G., Bianconi M., Summonte C.:
Surface doping of semiconductors by pulsed laser irradiation in reactive atmosphere.
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- Bhatia K.L., Krättschmer W., Kalbitzer S.:
Optical absorptivity of ion-beam irradiated silicon.
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Gas phase versus surface contributions to photolytic laser chemical vapor deposition rates.
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Laser-photoetching characteristics of polymers with dopants.
Appl. Phys. A 45/4, 277-288 (1988) PACS: 82.50E 82.65
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Appl. Phys. A 45/4, 325-335 (1988) PACS: 68.55 79.20 82.50
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Polysilicon dry etching by a large-area electron beam.
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Surface photovoltage spectroscopy for real n- and p-type (110) CdTe surfaces in the visible and near infra-red spectral range.
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- Fauster Th., Hartwig D., Dürr H.:
The determination of shadowing critical angles in impact collision ion scattering spectroscopy.
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A polarized neutron reflectometer for studying surface magnetism.
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- Foulon F., Fogarassy E., Slaoui A., Fuchs C., Unamuno S., Siffert P.:
Melting threshold of crystalline and amorphized Si irradiated with a pulsed ArF (193nm) excimer laser.
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Characterization of active layers in GaAs by microwave absorption.
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- Jiang J.-S., Yang X.-L., Chen L.-W., Zhou N.-F.:
A Mössbauer study on the surface hyperfine field of uniform hematite particles.
Appl. Phys. A 45/3, 245-247 (1988) PACS: 68.35 76.00
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248 nm laser etching of GaAs in chlorine and ozone gas environments.
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Laser-induced surface reduction of the High-Tc superconductor YBa₂Cu₃O(7-x).
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Sputtering of Cu atoms by Ar ions.
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Thin copper films by plasma CVD using copper-hexafluoro-acetylacetonate.
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Fundamental studies and device application of delta-doping in GaAs layers and in Al_xGa_{1-x}As/GaAs heterostructures.
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Diamond-like carbon films prepared by pulsed-laser evaporation.
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Blocking of silicon oxidation by low-dose nitrogen implantation.
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Ultraviolet laser ablation and etching of polymethyl methacrylate sensitized with an organic dopant.
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Laser-induced thermochemical maskless-etching of III-V compound semiconductors in chloride gas atmosphere.
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Multipole surface excitations on small oxide covered metal particles by fast electrons.
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